MMVL809T1

Silicon Tuning Diode

This device is designed for 900 MHz frequency control and tuning applications. It provides solid−state reliability in replacement of mechanical tuning methods.

Features

- Controlled and Uniform Tuning Ratio
- Surface Mount Package
- Available in 8 mm Tape and Reel
- Pb−Free Package is Available

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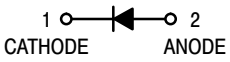
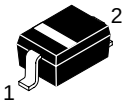
4.5 − 6.1 pF VOLTAGE VARIABLE CAPACITANCE DIODE





PLASTIC
SOD−323
CASE 477
STYLE 1

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	20	Vdc
Peak Forward Current	I_F	20	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board, T_A = 25°C (Note 1) Derate above 25°C	P_D	200 1.57	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	635	°C/W
Junction and Storage Temperature	T_J, T_{stg}	150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. FR−4 Minimum Pad

MARKING DIAGRAM

5K = Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)
*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMVL809T1	SOD−323	3000 / Tape & Reel
MMVL809T1G	SOD−323 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristics	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage (I_R = 10 μAdc)	$V_{(BR)R}$	20	–	–	Vdc
Reverse Voltage Leakage Current (V_R = 15 Vdc)	I_R	–	–	50	nAdc

	C_t, Diode Capacitance V_R = 2.0 Vdc, f = 1.0 MHz pF			**Q, Figure of Merit V_R = 3.0 Vdc f = 500 MHz**	**C_R, Capacitance Ratio C_2/C_8 (Note 2) f = 1.0 MHz**	
Device	**Min**	**Typ**	**Max**	**Typ**	**Min**	**Max**
MMVL809T1	4.5	5.3	6.1	75	1.8	2.6

2. C_R is the ratio of C_t measured at 2.0 Vdc divided by C_t measured at 8.0 Vdc.

TYPICAL CHARACTERISTICS

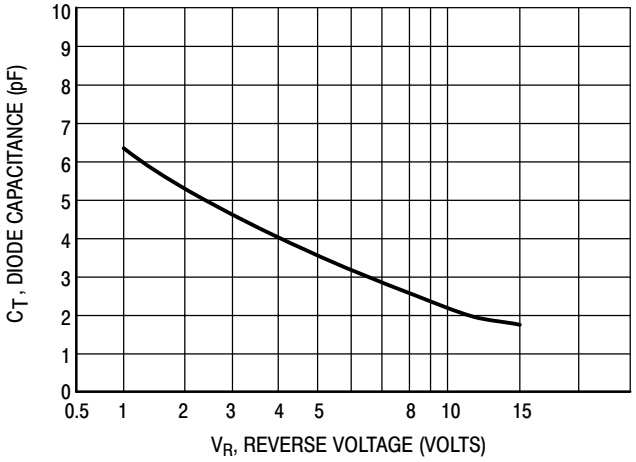


Figure 1. Diode Capacitance

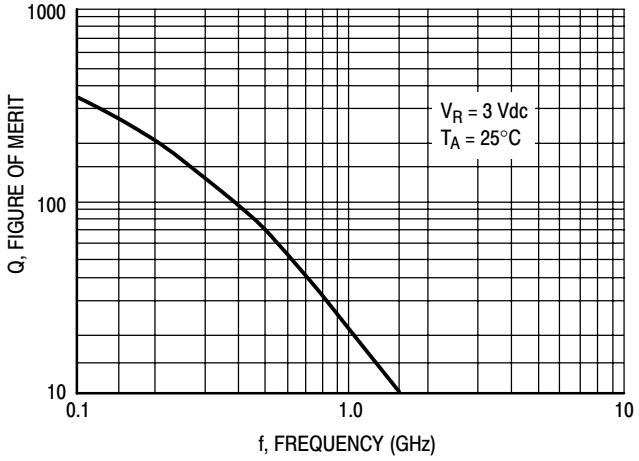


Figure 2. Figure of Merit

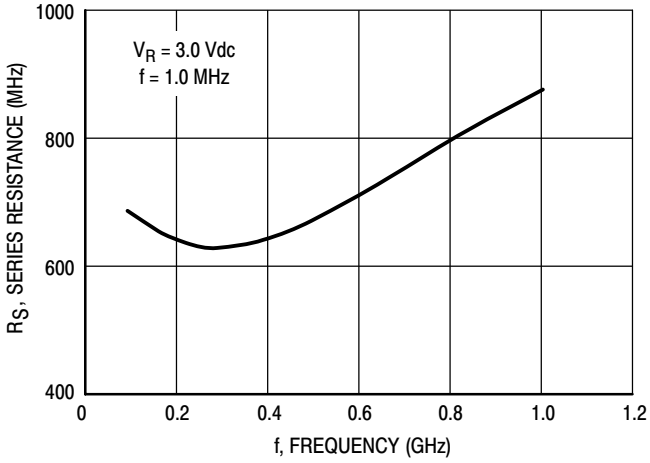


Figure 3. Series Resistance

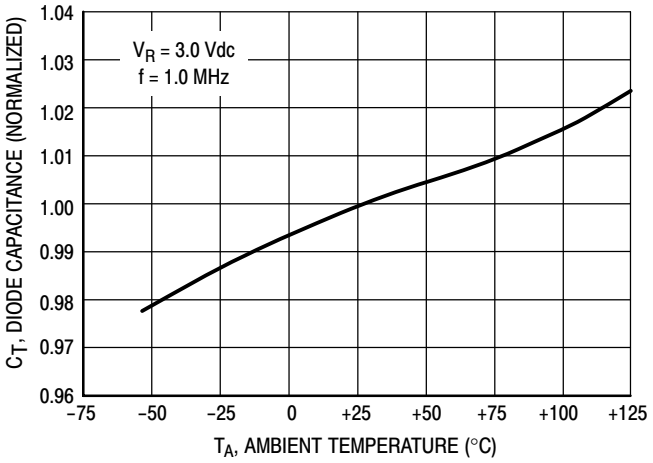
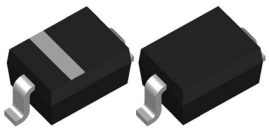
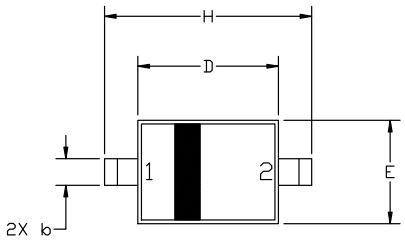


Figure 4. Diode Capacitance

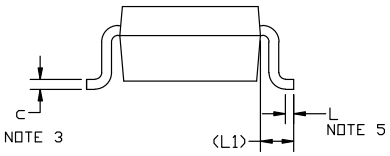


SOD−323 1.70x1.25x0.85
CASE 477
ISSUE K

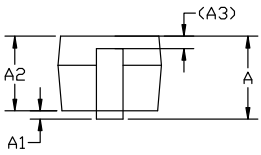
DATE 11 MAR 2024



TOP VIEW



SIDE VIEW

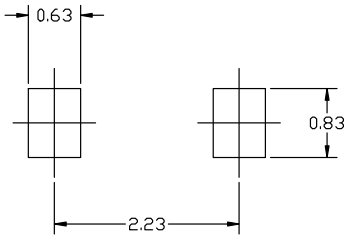


END VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
5. DIMENSION L IS MEASURE FROM END OF RADIUS.

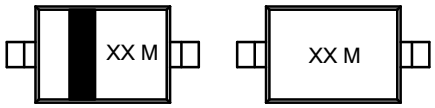
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.80	0.90	1.00
A1	0.00	0.05	0.10
A2	0.75	0.85	0.95
A3	0.15 (REF)		
b	0.25	0.32	0.4
c	0.09	0.12	0.18
D	1.60	1.70	1.80
E	1.15	1.25	1.35
H	2.30	2.50	2.70
L	0.08	---	---
L1	0.40 (REF)		



RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



STYLE 1 STYLE 2

XX = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. CATHODE (POLARITY BAND)
2. ANODE

STYLE 2:
NO POLARITY

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DESCRIPTION:	**SOD−323 1.70x1.25x0.85**		**PAGE 1 OF 1**

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